



Silicon NPN Planar RF Transistor

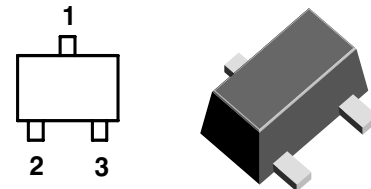
Description

The main purpose of this bipolar transistor is broadband amplification up to 2 GHz. In the space-saving 3-pin surface-mount SOT-490 package electrical performance and reliability are taken to a new level covering a smaller footprint on PC boards than previous packages. In addition to space savings, the SOT-490 provides a higher level of reliability than other 3-pin packages, such as more resistance to moisture. Due to the short length of its leads the SOT-490 is also reducing package inductances resulting in some bet-

ter electrical performance. All of these aspects make this device an ideal choice for demanding RF applications.

Features

- Low noise figure
- High transition frequency
- High power gain
- Small feedback capacitance
- Flat-lead SMD package
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



16867



Electrostatic sensitive device.
Observe precautions for handling.

Applications

Low noise small signal broadband applications, such as in satellite TV tuners, RF modules for wireless and mobile communications up to 2 GHz.

Mechanical Data

Typ: BFQ67F

Case: SOT-490 Plastic case

Weight: approx. 2.5 mg

Pinning: 1 = Collector, 2 = Base, 3 = Emitter

Parts Table

Part	Marking	Package
BFQ67F	V2	SOT-490

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Collector-base voltage		V_{CBO}	20	V
Collector-emitter voltage		V_{CEO}	10	V
Emitter-base voltage		V_{EBO}	2.5	V
Collector current		I_C	50	mA
Total power dissipation	$T_{amb} \leq 60\text{ }^{\circ}\text{C}$	P_{tot}	200	mW
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

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Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction ambient	1)	R_{thJA}	450	K/W

1) on glass fibre printed board (25 x 20 x 1.5) mm³ plated with 35 μm Cu

Electrical DC Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector-emitter cut-off current	V _{CE} = 20 V, V _{BE} = 0	I _{CES}			100	μA
Collector-base cut-off current	V _{CB} = 15 V, I _E = 0	I _{CBO}			100	nA
Emitter-base cut-off current	V _{EB} = 1 V, I _C = 0	I _{EBO}			1	μA
Collector-emitter breakdown voltage	I _C = 1 mA, I _B = 0	V _{(BR)CEO}	10			V
Collector-emitter saturation voltage	I _C = 50 mA, I _B = 5 mA	V _{CEsat}		0.1	0.4	V
DC forward current transfer ratio	V _{CE} = 5 V, I _C = 15 mA	h _{FE}	65	100	150	



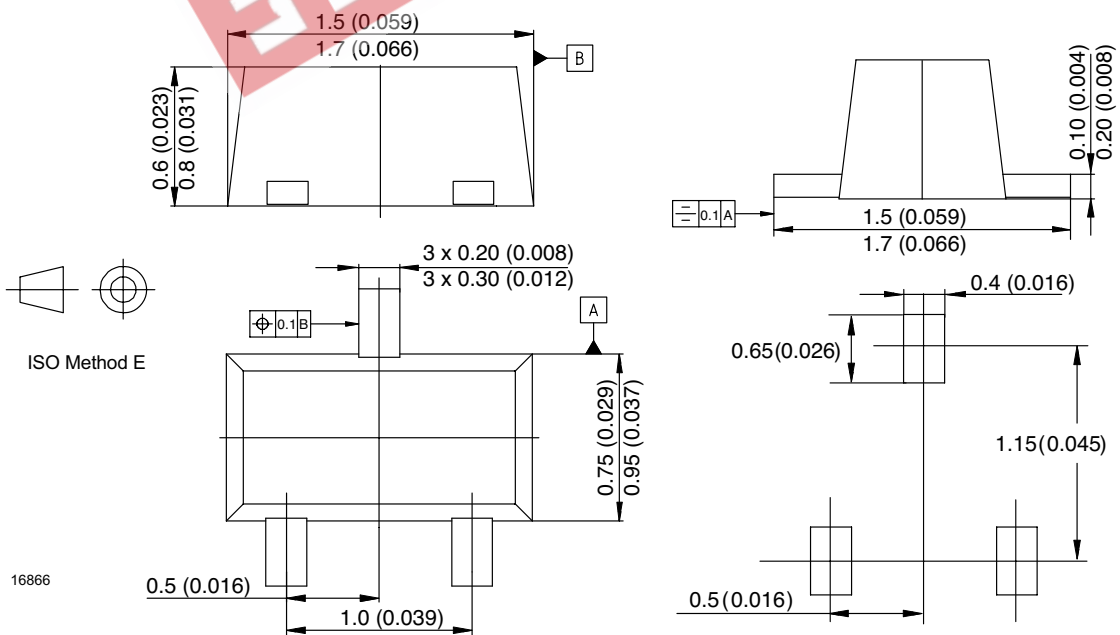


Electrical AC Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Transition frequency	V _{CE} = 8 V, I _C = 15 mA, f = 500 MHz	f _T		7.5		GHz
Collector-base capacitance	V _{CB} = 10 V, f = 1 MHz	C _{cb}		0.4		pF
Collector-emitter capacitance	V _{CE} = 8 V, f = 1 MHz	C _{ce}		0.2		pF
Emitter-base capacitance	V _{EB} = 0.5 V, f = 1 MHz	C _{eb}		0.85		pF
Noise figure	V _{CE} = 8 V, Z _S = Z _{Sopt} , f = 800 MHz, I _C = 5 mA	F		1.2		dB
	V _{CE} = 8 V, Z _S = 50 Ω, f = 2 GHz, I _C = 5 mA	F		2.5		dB
Power gain	V _{CE} = 8 V, Z _S = 50 Ω, Z _L = Z _{Lopt} , I _C = 15 mA, f = 800 MHz	G _{pe}		16		dB
	V _{CE} = 8 V, Z _S = 50 Ω, Z _L = Z _{Lopt} , I _C = 15 mA, f = 2 GHz	G _{pe}		8.5		dB
Transducer gain	V _{CE} = 8 V, I _C = 15 mA, f = 800 MHz, Z _O = 50 Ω	S _{21e} ²		15		dB
Linear output voltage - two tone intermodulation test	V _{CE} = 8 V, I _C = 15 mA, d _{IM} = 60 dB, f ₁ = 806 MHz, f ₂ = 810 MHz, Z _S = Z _L = 50 Ω	V ₁ = V ₂		160		mV
Third order intercept point	V _{CE} = 8 V, I _C = 15 mA, f = 800 MHz	IP ₃		26		dBm

Package Dimensions in mm



BFQ67F



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1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

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1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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